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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.015 grams (Approximate)

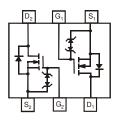






SOT26

Top View



Top View Internal Schematic

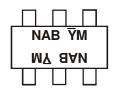
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2004DMK-7	SOT26	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



 $\begin{aligned} & \text{NAB} = \text{Marking Code} \\ & \text{YM} = \text{Date Code Marking} \\ & \overline{Y} = \text{Year (ex: T} = 2006) \\ & \text{M} = \text{Month (ex: 9} = \text{September)} \end{aligned}$

Date Code Kev

Year	2006	~	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	Т	~	D	Е	F	G	I	_	J	K	L	M
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

	Characteristic	Symbol	Value	Units	
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±8	V
Drain Current (Note 5)	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$	I _D	540 390	mA
Pulsed Drain Current (Note 6)			I _{DM}	1.5	Α

Thermal Characteristics (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_{D}	225	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Operating and Storage Temperature Range	$T_{J_i} T_{STG}$	-65 to +150	°C

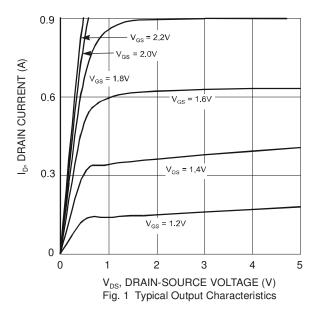
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)				•		
Drain-Source Breakdown Voltage	BV _{DSS}	20		_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 16V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±1	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.5		1.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
			0.4	0.55		$V_{GS} = 4.5V, I_D = 540mA$
Static Drain-Source On-Resistance	R _{DS(ON)}		0.5	0.70	Ω	$V_{GS} = 2.5V, I_D = 500mA$
			0.7	0.9		$V_{GS} = 1.8V, I_D = 350mA$
Forward Transfer Admittance	Y _{FS}	200	_	_	ms	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage (Note 7)	V _{SD}	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}			150	pF	101/1/
Output Capacitance				25	pF	V _{DS} = 16V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	C _{RSS}	_		20	pF	T = T.UIVII IZ

Notes:

- Device mounted on FR-4 PCB. Pulse width \leq 10 μ S, Duty Cycle \leq 1%. Short duration pulse test used to minimize self-heating effect.
- 7. Short duration pulse test used to minimize see.8. Guaranteed by design. Not subject to product testing.





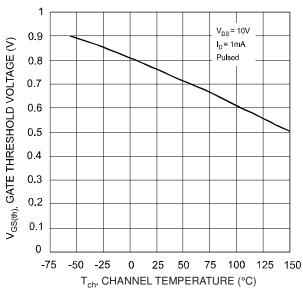


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

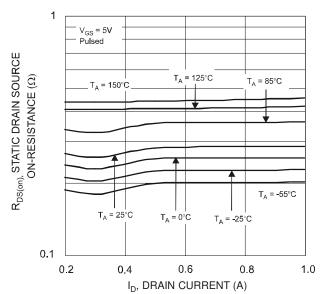


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

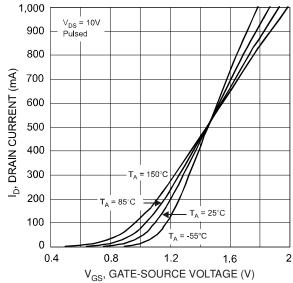


Fig. 2 Reverse Drain Current vs. Source-Drain Voltage

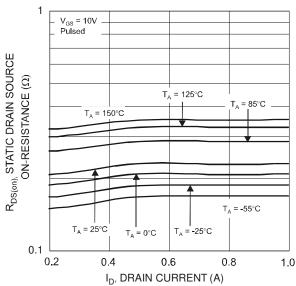


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

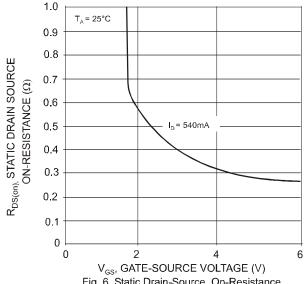


Fig. 6 Static Drain-Source, On-Resistance vs. Gate-Source Voltage



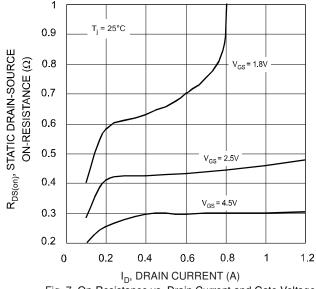
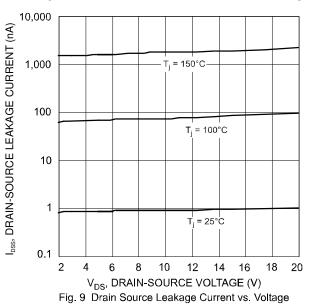


Fig. 7 On-Resistance vs. Drain Current and Gate Voltage



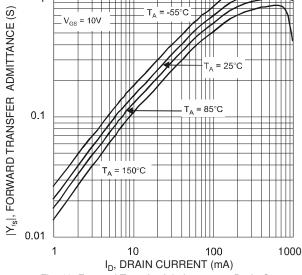


Fig. 11 Forward Transfer Admittance vs. Drain Current

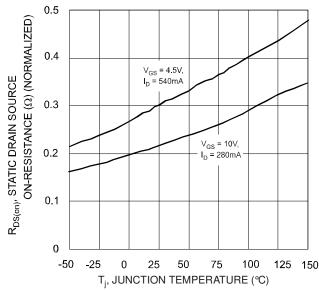


Fig. 8 Static Drain-Source, On-Resistance vs. Temperature

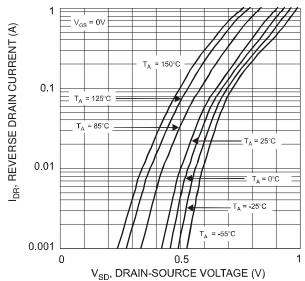
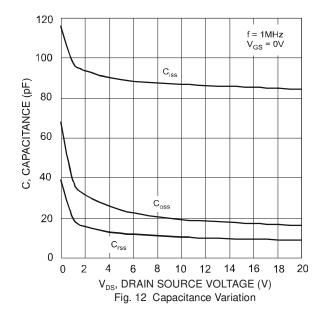


Fig. 10 Reverse Drain Current vs. Source-Drain Voltage

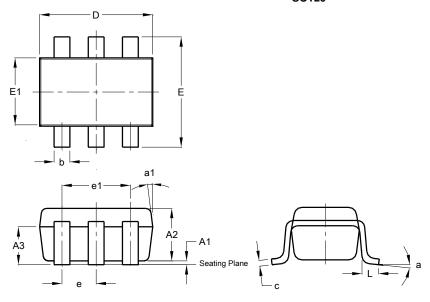




Package Outline Dimensions

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

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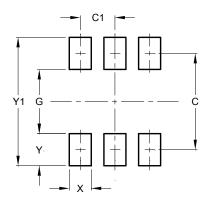


SOT26						
Dim	Min	Max	Тур			
A1	0.013	0.10	0.05			
A2	1.00	1.30	1.10			
A3	0.70	0.80	0.75			
b	0.35	0.50	0.38			
С	0.10	0.20	0.15			
D	2.90	3.10	3.00			
е	-	-	0.95			
e1	-	-	1.90			
Е	2.70	3.00	2.80			
E1	1.50	1.70	1.60			
L	0.35	0.55	0.40			
а	_	_	8°			
a1	_	_	7°			
All Dimensions in mm						

Suggested Pad Layout

 $Please see AP02001 \ at \ http://www.diodes.com/_files/datasheets/ap02001.pdf \ for \ the \ latest \ version.$

SOT26



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Υ	0.80
Y1	3.20



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